

Refine Search

Search Results -

Terms	Documents
semiconductor and (((trench or groove) near3 fill) same liquid)	1

Database:

- US Pre-Grant Publication Full-Text Database
- US Patents Full-Text Database
- US OCR Full-Text Database
- EPO Abstracts Database
- JPO Abstracts Database
- Derwent World Patents Index
- IBM Technical Disclosure Bulletins

Search:

L22

Refine Search

Recall Text

Clear

Interrupt

Search History

DATE: Tuesday, July 19, 2005 [Printable Copy](#) [Create Case](#)

<u>Set Name</u> side by side	<u>Query</u>	<u>Hit Count</u>	<u>Set Name</u> result set
	<i>DB=TDBD; PLUR=YES; OP=ADJ</i>		
<u>L22</u>	semiconductor and (((trench or groove) near3 fill) same liquid)	1	<u>L22</u>
	<i>DB=DWPI; PLUR=YES; OP=ADJ</i>		
<u>L21</u>	semiconductor and (((trench or groove) near3 fill) same liquid)	17	<u>L21</u>
	<i>DB=JPAB; PLUR=YES; OP=ADJ</i>		
<u>L20</u>	semiconductor and (((trench or groove) near3 fill) same liquid)	22	<u>L20</u>
	<i>DB=EPAB; PLUR=YES; OP=ADJ</i>		
<u>L19</u>	semiconductor and (((trench or groove) near3 fill) same liquid)	0	<u>L19</u>
	<i>DB=USPT; PLUR=YES; OP=ADJ</i>		
<u>L18</u>	semiconductor and (((trench or groove) near3 fill) same liquid)	150	<u>L18</u>
	<i>DB=PGPB; PLUR=YES; OP=ADJ</i>		
<u>L17</u>	semiconductor and (((trench or groove) near3 fill) same liquid)	95	<u>L17</u>
<u>L16</u>	20040266153	1	<u>L16</u>
<u>L15</u>	20040209484	1	<u>L15</u>
<u>L14</u>	20030129826	1	<u>L14</u>
<u>L13</u>	20030032281	1	<u>L13</u>

<u>L12</u>	200300322281	0	<u>L12</u>
<u>L11</u>	20020018849	1	<u>L11</u>
<u>L10</u>	20020000195	1	<u>L10</u>
<u>L9</u>	20010041250	1	<u>L9</u>
<u>L8</u>	2001/0041250	0	<u>L8</u>
<i>DB=DWPI; PLUR=YES; OP=ADJ</i>			
<u>L7</u>	2001/0041250	0	<u>L7</u>
<i>DB=JPAB; PLUR=YES; OP=ADJ</i>			
<u>L6</u>	(self aligned) and silicide and (SiGe or (silicon adj germanium)) and metal and ((thermal or heat\$) near3 anneal\$)	0	<u>L6</u>
<i>DB=EPAB; PLUR=YES; OP=ADJ</i>			
<u>L5</u>	(self aligned) and silicide and (SiGe or (silicon adj germanium)) and metal and ((thermal or heat\$) near3 anneal\$)	0	<u>L5</u>
<i>DB=USPT; PLUR=YES; OP=ADJ</i>			
<u>L4</u>	(self aligned) and silicide and (SiGe or (silicon adj germanium)) and metal and ((thermal or heat\$) near3 anneal\$)	322	<u>L4</u>
<i>DB=PGPB; PLUR=YES; OP=ADJ</i>			
<u>L3</u>	(self aligned) and silicide and (SiGe or (silicon adj germanium)) and metal and ((thermal or heat\$) near3 anneal\$)	246	<u>L3</u>
<i>DB=TDBD; PLUR=YES; OP=ADJ</i>			
<u>L2</u>	(self aligned) and silicide and (SiGe or (silicon adj germanium)) and metal and ((thermal or heat\$) near3 anneal\$)	1	<u>L2</u>
<i>DB=DWPI; PLUR=YES; OP=ADJ</i>			
<u>L1</u>	(self aligned) and silicide and (SiGe or (silicon adj germanium)) and metal and ((thermal or heat\$) near3 anneal\$)	3	<u>L1</u>

END OF SEARCH HISTORY

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	(isolation adj trench) and (liquid adj deposition) and (solid adj deposition)". clm"	USPAT	ADJ	ON	2005/07/19 14:17
L2	1419	(438/424,427,431).CCLS.	USPAT	OR	OFF	2005/07/19 14:17